

AMENDMENTS TO THE CLAIMS

1. **(Original)** A substrate processing system for processing a substrate, comprising:
a carrier gas source;
a liquid source container;
a reactor;
a vaporization chamber comprising a body that forms a first inner surface that defines at least in part a cavity, the cavity being in communication with the carrier gas source through a gas line, the liquid source container through a supply line and the reactor through a feed line, the first inner surface being made from a first material that is non-ferric; and
a transition piece having a first surface made from the first material and a second surface made from a second material that is ferric; wherein a connection between the vaporization chamber and at least one of the gas line, the supply line and the feed line extends from the first surface to the second surface and through the body of the vaporization chamber to the cavity, the connection including a connector that is attached to the second surface of the transition piece.
2. **(Original)** A substrate processing system as in Claim 1, wherein the first material is aluminum.
3. **(Original)** A substrate processing system as in Claim 2, wherein the second material is stainless steel.
4. **(Currently amended)** A substrate processing system as in Claim ~~[[4]]~~ 1, wherein the liquid source container contains liquid trisilane.
5. **(Currently amended)** A substrate processing system as in Claim ~~[[5]]~~ 4, wherein the carrier gas source contains hydrogen gas.
6. **(Original)** A substrate processing system as in Claim 1, wherein the second material is stainless steel.
7. **(Original)** A substrate processing system as in Claim 1, wherein the transition piece is welded to the body of the vaporization chamber.
8. **(Original)** A substrate processing system as in Claim 1, wherein the vaporization chamber includes a liquid level sensing device.

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9. **(Original)** A substrate processing system as in Claim 8, wherein the liquid level sensing device is configured to sense the capacitance difference between a liquid source material and a vaporized source material.

10. **(Original)** A substrate processing system as in Claim 9, wherein the liquid and vaporized source material is trisilane.

11. **(Original)** The substrate processing system as in Claim 1, wherein the transition member comprises a first member and a second member, the first member being formed, at least in part, from the first material and the second member being formed, at least in part, from the second material.

12. **(Original)** The substrate processing system as in Claim 11, wherein the second member comprises a first layer of the first material that has been explosion bonded to the second member, the first member being explosion bonded to the first layer of the second member.

13. **(Original)** The substrate processing system as in Claim 12, wherein the first layer is mechanically cladded to a second layer of the second material, the second layer being explosion bonded to the second member.

14. **(Original)** The substrate processing system as in Claim 1, wherein the vaporization chamber is a bubbler.

15-28. **(Canceled)**